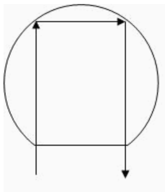
| Part Number | Customer |
|---|---|

| **Category** | | **Parameter** | **Specification** | **Measurement Method** |
|---|---|---|---|---|
| OverallWafer | 1.0 | Diameter | 150.00 +/- 0.20 mm | |
| | 2.0 | Primary Flat Orientation | {110} +/- 1 degree | Customer supplied material |
| | 3.0 | Primary Flat Length | 57.50 +/- 2.50 mm | Customer supplied material |
| | 4.0 | Secondary Flat Orientation | None | Customer supplied material |
| | 5.0 | Overall Thickness | 301.00 +/- 5.00 µm | ADE, 100% |
| | 6.0 | Total Thickness Variation (TTV) | <2.00µm | Guaranteed by Process |
| | 7.0 | Bow | <60.00µm | Estimate. ADE to ASTM F534, 100% |
| | 8.0 | Warp | <60.00µm | Estimate. ADE to ASTM F534, 100% |
| | 9.0 | Edge Chips | 0 | Bright Light, 100% |
| | 10.0 | Edge Exclusion | 5mm | |
| HandleSilicon | 11.0 | Handle Growth Method | CZ | Customer supplied material |
| | 12.0 | Handle Orientation | {100} +/- 0.5 degree | Customer supplied material |
| | 13.0 | Handle Thickness | 290.00 +/- 4.00 µm | ADE, 100% |
| | 14.0 | Handle Doping Type | N | Customer supplied material |
| | 15.0 | Handle Dopant | Phos | Customer supplied material |
| | 16.0 | Handle Resistivity | 1~30 Ohm-cm | Customer supplied material |
| | 17.0 | Backside Finish | Polished with 1um OXIDE, lasermark and light handling marks | Guaranteed by process |
| BuriedOxide | 18.0 | Oxide Type | Thermal | |
| | 19.0 | Oxide Thickness | 10,000.00 +/- 500.00 A | Nanospec 5pts , 4% |
| | 20.0 | Oxide formed on | Handle | |
| DeviceSilicon | 21.0 | Device Growth Method | CZ | Customer supplied material |
| | 22.0 | Device Orientation | {100} +/- 0.5 degree | Customer supplied material |
| | 23.0 | Nominal Thickness | 10.00 +/- 0.50 µm | Filmetrics 9pts, 100% (note3) |
| | 24.0 | Distance to device silicon edge from wafer edge | < 2mm | Typical by Process |
| | 25.0 | Device Doping Type | N | Customer supplied material |
| | 26.0 | Device Dopant | Phos | Customer supplied material |
| | 27.0 | Device Resistivity | 1-30 Ohm-cm | Customer supplied material |
| | 28.0 | Surface Voids | None | Bright Light, 100% (note2) |
| | 29.0 | Haze | None | Bright Light, 100% (note2) |
| | 30.0 | Scratches | none on the front-side | Bright Light, 100% (note2) |

| **Category** | **Parameter** | **Specification** | **Measurement Method** |
|---|---|---|---|
| Shipping Details | Wafer per box : | Max 25 | |
| | Packaging : | Taped Polypropylene Wafer Box<br>Empak, Ultrapak, 150.00mm<br>Antistatic Double Bagging | |
| | Lot Shipment Data | Device Thickness<br>Bow / Warp Data<br>Handle and SOI Thickness | |

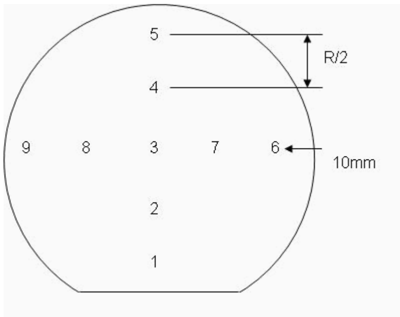
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information